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Kind regards,

Team Nexperia



PNP 500 mA, 50 V resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Rev. 3 — 22 September 2010

Product data sheet

1. Product profile

1.1 General description

500 mA PNP Resistor-Equipped Transistor (RET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTD123ET.

1.2 Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

1.4 Quick reference data

Table 1. Quick reference data

Symbol Conditions Unit Parameter Min Тур Max VCEO collector-emitter voltage open base ---50 V I_{O} output current --500 mΑ -R1 2.2 2.86 bias resistor 1 (input) 1.54 kΩ R2/R1 bias resistor ratio 0.9 1.0 1.1

- Reduces pick and place costs
- ±10 % resistor ratio tolerance
- AEC-Q101 qualified
- Cost-saving alternative for BC807 series in digital applications
- Switching loads



PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	input (base)	_	
2	GND (emitter)	3	3
3	output (collector)	1 2 006aaa144	

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PDTB123ET	-	plastic surface-mounted package; 3 leads	SOT23	

4. Marking

Table 4.	Marking codes		
Type num	nber	Marking code ^[1]	
PDTB123ET		*7S	
[4] *	ando in Hong Kong		

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong * = t: made in Malaysia
 - * = W: made in China
 - = w. made in China

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-12	V
lo	output current		-	-500	mA

PDTB123ET Product data sheet

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Limiting values ... continued Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

Thermal characteristics 6.

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Characteristics 7.

$T_{amb} = 25$ °C unless otherwise specified. Symbol Parameter Conditions Unit Min Тур Max collector-base $V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}$ _ -100 nA I_{CBO} cut-off current $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$ -100 -nA $V_{CE} = -50 \text{ V}; I_B = 0 \text{ A}$ **I**CEO collector-emitter -_ -0.5 μΑ cut-off current $V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$ emitter-base -2.0 mΑ I_{EBO} -cut-off current DC current gain $V_{CE} = -5 V;$ 40 h_{FE} -- $I_{\rm C} = -50 \, {\rm mA}$ collector-emitter $I_{C} = -50 \text{ mA};$ V V_{CEsat} -0.3-saturation voltage $I_B = -2.5 \text{ mA}$ off-state input voltage $V_{CE} = -5 V;$ V_{I(off)} -0.6 -1.1 -1.8٧ $I_{\rm C} = -100 \ \mu A$ V_{I(on)} $V_{CE} = -0.3 V;$ -2.0V on-state input voltage -1.0 -1.5 $I_C = -20 \text{ mA}$ R1 bias resistor 1 (input) 1.54 2.2 2.86 kΩ R2/R1 bias resistor ratio 0.9 1.0 1.1 collector capacitance 11 C_{c} $V_{CB} = -10 V;$ pF - $I_E = i_e = 0 A;$ f = 100 MHz

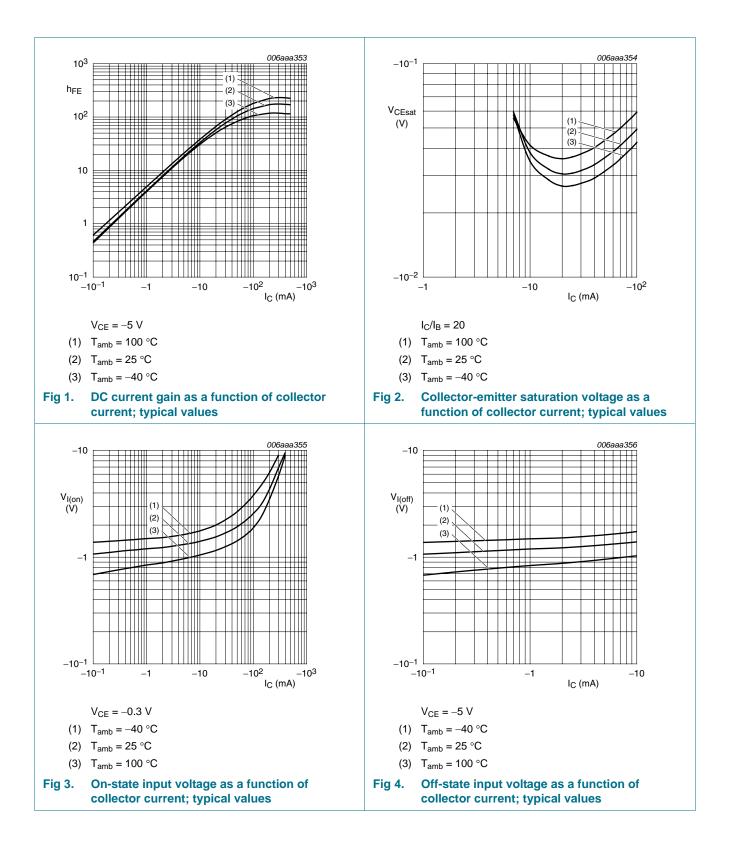
Table 7. **Characteristics**

PDTB123ET Product data sheet

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PDTB123ET

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω



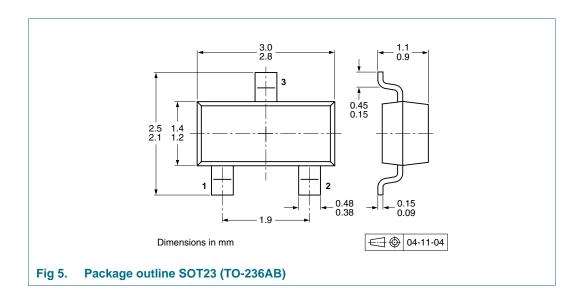
PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

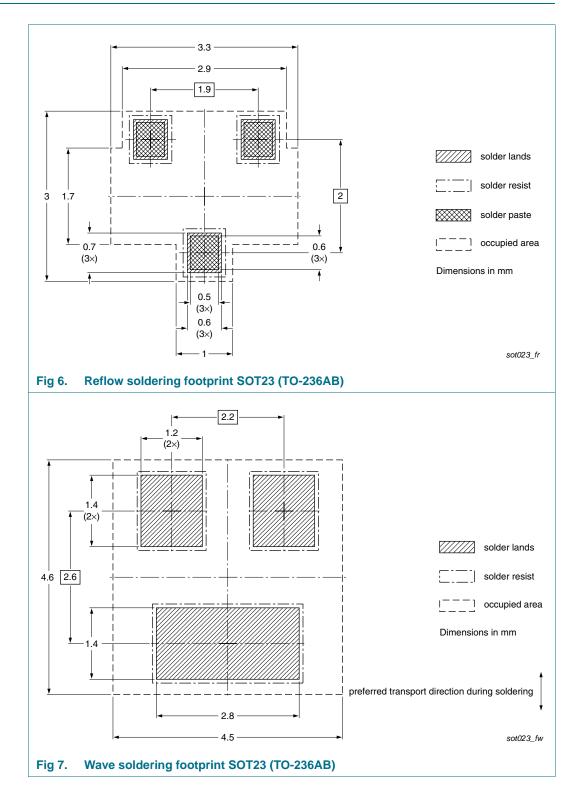
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	cription Packing quantity	
			3000	10000
PDTB123ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 14.

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

11. Soldering



PDTB123ET

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

12. Revision history

Table 9. Revision h	istory				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTB123ET v.3	20100922	Product data sheet	-	PDTB123E_SER_2	
Modifications:	 Type number 	ers PDTB123EK and PDTB	123ES deleted.		
	 <u>Table 7 "Characteristics"</u>: unit for V_{CEsat} changed from mV to V. 				
	 <u>Section 8 "Test information"</u>: added. 				
	Section 11 "	Soldering": added.			
	 Section 13 " 	Legal information": updated	l.		
PDTB123E_SER_2	20091116	Product data sheet	-	PDTB123E_SER_1	
PDTB123E_SER_1	20050427	Product data sheet	-	-	

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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PDTB123ET

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

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